In the Claims

Claims 1-31 are canceled.

32. [Original] A method of sensing temperature of an electronic device workpiece comprising:

providing an electronic device workpiece;

supporting a temperature sensing device using the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece;

electrically coupling the electrical interconnect with the temperature sensing device; and

sensing temperature of the electronic device workpiece using the temperature sensing device.

33. [Original] The method according to claim 32 further comprising wire bonding the electrical interconnect and the temperature sensing device.

34. [Original] The method according to claim 32 further comprising:

forming a cavity in the electronic device workpiece; and

providing the temperature sensing device within the cavity.

35. [Original] The method according to claim 34 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

36. [Original] The method according to claim 34 wherein the forming the cavity comprises isotropically etching the electronic device workpiece.

37. [Original] The method according to claim 32 further comprising forming the temperature sensing device.

38. [Original] The method according to claim 37 wherein the forming the temperature sensing device comprises forming a resistance temperature device.

39. [Original] The method according to claim 32 further comprising electrically coupling the electrical interconnect with external circuitry.

40. [Original] The method according to claim 32 further comprising electrically coupling the temperature sensing device with an edge of the electronic device workpiece using the electrical interconnect.

41. [Original] The method according to claim 32 wherein the providing the electrical interconnect comprises forming a conductive trace.

42. [Original] The method according to claim 32 further comprising contacting the electrical interconnect with the temperature sensing device.

43. [Previously Presented] The method according to claim 32 wherein the sensing comprises sensing temperature of the electronic device workpiece comprising a semiconductive wafer.

Claims 44-52 are canceled.

53. [Previously Presented] A method of sensing temperature of an electronic device workpiece comprising:

providing an electronic device workpiece;

forming a temperature sensing device over the electronic device workpiece, the forming including providing the temperature sensing device in a temperature sensing relation with the electronic device workpiece; and

sensing the temperature of the electronic device workpiece using the temperature sensing device.

54. [Original] The method according to claim 53 further comprising:

providing an electrical interconnect upon the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device.

55. [Original] The method according to claim 54 wherein the providing the electrical interconnect comprises forming a conductive trace.

56. [Original] The method according to claim 54 wherein the electrically coupling comprises wire bonding the electrical interconnect and the temperature sensing device.

57. [Original] The method according to claim 54 wherein the electrically coupling includes contacting the electrical interconnect and the temperature sensing device.

58. [Original] The method according to claim 53 further comprising:

forming a cavity in the electronic device workpiece; and

providing the temperature sensing device within the cavity.

59. [Original] The method according to claim 58 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

60. [Original] The method according to claim 53 wherein the forming comprises forming a resistance temperature device.

61. [Original] The method according to claim 53 further comprising forming plural temperature sensing devices upon the electronic device workpiece.

62. [Original] A method of sensing temperature of an electronic device workpiece comprising:

providing an electronic device workpiece;

supporting a temperature sensing device using the electronic device workpiece;

providing the temperature sensing device in a temperature sensing relation with the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device.

63. [Original] The method according to claim 62 wherein the coupling comprises wire bonding the electrical interconnect and the temperature sensing device.

64. [Original] The method according to claim 62 wherein the coupling comprises contacting the electrical interconnect with the temperature sensing device.

65. [Original] The method according to claim 62 further comprising:

forming a cavity in the electronic device workpiece; and

providing the temperature sensing device within the cavity.

66. [Original] The method according to claim 65 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

67. [Currently Amended] The method according to claim 62 further comprising forming [[a]] the temperature sensing device upon the electronic device workpiece.

68. [Original] The method according to claim 62 further comprising electrically coupling the electrical interconnect with circuitry external to the electronic device workpiece.

69. [Original] The method according to claim 62 further comprising electrically coupling the temperature sensing device with an edge of the electronic device workpiece using the electrical interconnect.

70. [Original] The method according to claim 62 wherein the providing the electrical interconnect comprises forming a conductive trace.

71. [Previously Presented] A temperature sensing method comprising:

supporting a temperature sensing device using a wafer;

providing the temperature sensing device in a temperature sensing relationship with respect to the wafer;

exposing the wafer and the temperature sensing device to process conditions effective to form at least one electronic device; and

sensing a temperature of the wafer using the temperature sensing device during the exposing.

72. [Previously Presented] The method of claim 71 further comprising adjusting the process conditions responsive to the sensing.

73. [Previously Presented] The method of claim 71 further comprising sensing the temperature of the wafer at a plurality of positions covering substantially an entirety of a surface of the wafer.

74. [Previously Presented] The method of claim 71 wherein the sensing comprises sensing temperature in three dimensions of the wafer.

75. [Previously Presented] The method of claim 71 wherein the wafer comprises a production wafer, and further comprising forming the at least one electronic device using the wafer responsive to the exposing.

76. [New] The method according to claim 32 wherein the providing the electronic device workpiece comprises providing a wafer comprising silicon.

77. [New] The method according to claim 32 wherein the sensing comprises sensing the temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

78. [New] The method according to claim 53 wherein the providing the electronic device workpiece comprises providing a wafer comprising silicon.

79. [New] The method according to claim 53 wherein the sensing comprises sensing the temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

80. [New] The method according to claim 62 wherein the providing the electronic device workpiece comprises providing a wafer comprising silicon.

81. New] The method according to claim 62 further comprising sensing temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

82. [New] The method of claim 71 wherein the supporting comprises supporting the temperature sensing device using the wafer comprising silicon.

83. [New] The method of claim 71 wherein the sensing the temperature comprises sensing the temperature of the wafer during fabrication of an electronic device using the wafer.